DSC7102

Silicon NPN epitaxial planar type

For low frequency amplification Complementary to DSA7102

■ Features

- \bullet Low collector-emitter saturation voltage $V_{\text{CE(sat)}}$
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL: Level 1 compliant)

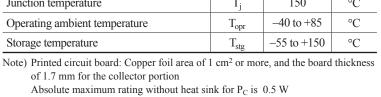
■ Marking Symbol: 5D

■ Packaging

DSC7102×0L Embossed type (Thermo-compression sealing): 1 000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	80	V	
Collector-emitter voltage (Base open)	V _{CEO}	80	V	
Emitter-base voltage (Collector open)	V _{EBO}	5	V	
Collector current	I_{C}	1	A	
Peak collector current	I_{CP}	1.5	A	
Collector power dissipation	P _C	1	W	
Junction temperature	T _j	150	°C	
Operating ambient temperature	T _{opr}	-40 to +85	°C	
Storage temperature	T _{stg}	-55 to +150	°C	



Unit: mm 4.5 1.6 0.41 0.5 0.4 1.5 3.0 1: Base 2: Collector 3: Emitter MiniP3-F2-B Panasonic **JEITA** SC-62 Code TO-243

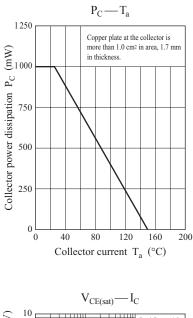
■ Electrical Characteristics $T_a = 25$ °C±3°C

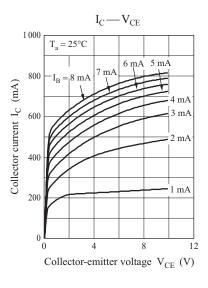
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = 10 \ \mu A, I_{\rm E} = 0$	80			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = 1 \text{ mA}, I_B = 0$	80			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = 10 \mu A, I_C = 0$	5			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 40 \text{ V}, I_{E} = 0$			0.1	μΑ
Forward current transfer ratio *1	h _{FE1} *2	$V_{CE} = 2 \text{ V}, I_{C} = 100 \text{ mA}$	120		340	
	h _{FE2}	$V_{CE} = 2 \text{ V}, I_{C} = 500 \text{ mA}$	60			_
Collector-emitter saturation voltage *1	V _{CE(sat)}	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		0.15	0.30	V
Base-emitter saturation voltage *1	V _{BE(sat)}	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		0.9	1.2	V
Transition frequency	f_T	$V_{CE} = 10 \text{ V}, I_{C} = 50 \text{ mA}$		180		MHz
Collector output capacitance (Common base, input open circuited)	C _{ob}	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		8	20	pF

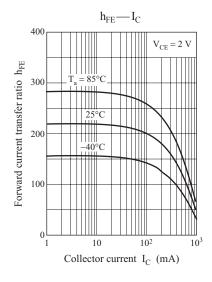
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

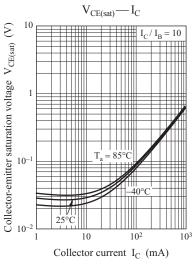
- 2. *1: Pulse measurement
 - *2: Rank classification

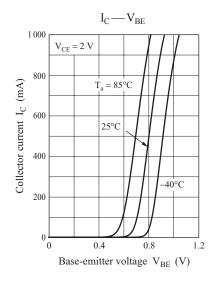
Code	R	S	
Rank	R	S	
h_{FE1}	120 to 240	170 to 340	
Marking Symbol	5DR	5DS	

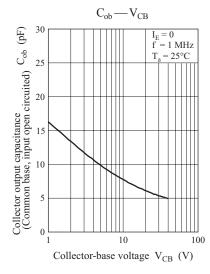


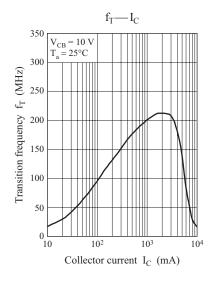


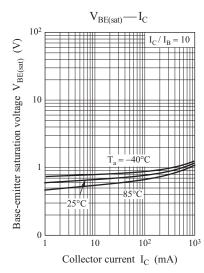








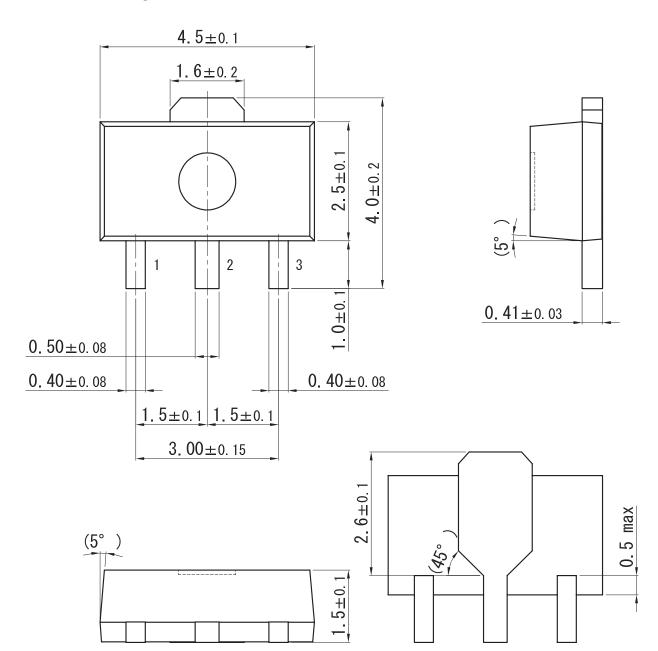




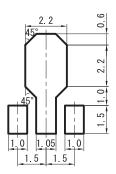
Ver. DED 2

MiniP3-F2-B

Unit: mm



■ Land Pattern (Reference) (Unit: mm)



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